

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 211810US99		SERIAL NO. 09/911,495	
LIST OF REFERENCES CITED BY APPLICANT  FEB 06 2002 PATENT & TRADEMARK OFFICE				APPLICANT BARBARA F. BARENBURG ET AL			
				FILING DATE JULY 25, 2001		GROUP 2813	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
SBG	AA	4,174,422	11/13/79	Matthews et al.			
SBG	AB	4,523,211	06/11/85	Morimoto et al.			
SBG	AC	4,661,176	04/28/87	Manasevit			
SBG	AD	4,793,872	12/27/88	Meunier et al.			
SBG	AE	4,855,249	08/08/89	Akasaki et al.			
SBG	AF	4,912,087	03/27/90	Aslam et al.			
SBG	AG	5,173,474	12/22/92	Connell et al.			
SBG	AH	5,358,925	10/25/94	Neville Connell et al.			
SBG	AI	5,393,352	02/28/95	Summerfelt			
SBG	AJ	5,418,216	05/23/95	Fork			
SBG	AK	5,450,812	09/19/95	McKee et al.			
SBG	AL	5,478,653	12/26/95	Guenzer			
SBG	AM	5,482,003	01/09/96	McKee et al.			
SBG	AN	5,514,484	05/07/96	Nashimoto			
SBG	AO	5,588,995	12/31/96	Sheldon			
SBG	AP	5,733,641	03/31/98	Fork et al.			
SBG	AQ	5,830,270	11/03/98	McKee et al.			
SBG	AR	5,912,068	06/15/99	Jia			
SBG	AS	6,020,222	02/01/00	Wollesen			
SBG	AT	6,064,092	05/16/00	Park			
SBG	AU	6,096,584	08/01/00	Ellis-Monaghan et al.			
SBG	AV	6,136,666	10/24/00	So			
SBG	AW	6,174,755	01/16/01	Manning			
SBG	AX	6,180,486	01/30/01	Leobandung et al.			
SBG	AY	3,802,967	04/09/74	Ladany et al.			
SBG	AZ	4,404,265	09/13/83	Manasevit			
SBG	BA	4,482,906	11/13/84	Hovel et al.			
SBG	BB	4,846,926	07/11/89	Kay et al.			
SBG	BC	4,891,091	01/02/90	Shastri			
SBG	BD	4,928,154	05/22/90	Umeno et al.			
SBG	BE	4,963,949	10/16/90	Wanlass et al.			
SBG	BF	5,141,894	08/25/92	Bisaro et al.			
SBG	BG	5,159,413	10/27/92	Calviello et al.			
SBG	BH	5,221,367	06/22/93	Chisholm et al.			
SBG	BI	5,225,031	07/06/93	McKee et al.			
SBG	BJ	5,556,463	09/17/96	Guenzer			
SBG	BK	5,670,798	09/23/97	Schetzina			
SBG	BL	5,735,949	04/07/98	Mantl et al.			
SBG	BM	5,741,724	04/21/98	Ramdani et al.			
SBG	BN	5,810,923	09/22/98	Yano et al.			
SBG	BO	6,045,626	04/04/00	Yano et al.			
SBG	BP	6,064,078	05/16/00	Northrup et al.			
SBG	BQ	6,103,008	08/15/00	McKee et al.			

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SBG	CA	6,107,653	08/22/00	Fitzgerald			
SBG	CB	6,113,690	09/05/00	Yu et al.			
SBG	CC	6,143,072	11/07/00	McKee et al.			
SBG	CD	5,155,658	10/13/92	Inam et al.			
SBG	CE	5,248,564	09/28/93	Ramesh			
SBG	CF	5,270,298	12/14/93	Ramesh			
SBG	CG	5,418,389	05/23/95	Watanabe			
SBG	CH	6,055,179	04/25/00	Koganei et al.			
SBG	CI	5,326,721	07/05/94	Summerfelt			
SBG	CJ	5,310,707	05/10/94	Oishi et al.			
SBG	CK	4,999,842	03/12/91	Huang et al.			
SBG	CL	5,874,860	02/23/99	Brunel et al.			
SBG	CM	6,002,375	12/14/99	Corman et al.			
SBG	CN	4,802,182	01/31/89	Thornton et al.			
SBG	CO	4,284,329	08/18/81	Smith et al.			
SBG	CP	4,006,989	02/08/77	Andringa			
SBG	CQ	5,729,641	03/17/98	Chandonnet et al.			
SBG	CR	5,640,267	06/17/97	May et al.			
SBG	CS	5,576,879	11/19/96	Nashimoto			
SBG	CT	5,528,414	06/18/96	Oakley			
SBG	CU	4,802,182	01/31/89	Thornton et al.			
SBG	CV	5,436,759	07/25/95	Dijaii et al.			
SBG	CW	6,128,178	10/03/00	Newns			
SBG	CX	6,121,642	09/19/00	Newns			
SBG	CY	5,926,496	07/20/99	Ho et al.			
SBG	CZ	5,790,583	08/04/98	Ho			
SBG	DA	5,825,799	10/20/98	Ho et al.			
SBG	DB	5,857,049	01/05/99	Beranek et al.			
SBG	DC	6,184,144B1	02/06/01	Lo			
SBG	DD	5,981,400	11/09/99	Lo			
SBG	DE	5,286,985	02/15/94	Taddiken			
SBG	DF	3,766,370	10/16/73	Walther			
SBG	DG	4,777,613	10/11/98	Shahan et al.			
SBG	DH	5,990,495	11/23/99	Ohba			
SBG	DI	5,081,062	01/14/92	Vasudev et al.			
SBG	DJ	5,404,581	04/04/95	Honjo			
SBG	DK	4,896,194	01/23/90	Suzuki			
SBG	DL	5,606,184	02/25/97	Abrokwhah, et al.			
SBG	DM	5,060,031	10/22/91	Abrokwhah, et al.			
SBG	DN	6,114,996	09/05/00	Nghiem			
SBG	DO	4,882,300	11/21/89	Inoue et al.			
SBG	DP	5,674,366	10/07/97	Hayashi et al.			
SBG	DQ	6,173,474	01/16/01	Conrad			

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SBG	EA	5,731,220	03/24/98	Tsu et al.			
SBG	EB	5,828,080	10/27/98	Yano et al.			
SBG	EC	5,801,105	09/01/98	Yano et al.			
SBG	ED	4,484,332	11/20/84	Hawrylo			
SBG	EE	4,815,084	03/21/89	Scifres et al.			
SBG	EF	5,293,050	03/08/94	Chapple-Sokol et al			
SBG	EG	6,222,654	04/24/01	Frigo			
SBG	EH	5,937,285	08/10/99	Abrokwhah et al.			
SBG	EI	5,116,461	05/26/92	Lebby et al.			
SBG	EJ	5,640,267	06/17/97	May et al.			
SBG	EK	5,442,191	08/15/95	Ma			
SBG	EL	6,008,762	12/28/99	Nghiem			
SBG	EM	5,444,016	08/22/95	Abrokwhah, et al.			
SBG	EN	5,614,739	03/25/97	Abrokwhah et al.			
SBG	EO	5,480,829	01/02/96	Abrokwhah, et al.			
SBG	EP	5,144,409	09/01/92	Ma			
SBG	EQ	6,058,131	05/02/00	Pan			
SBG	ER	5,995,359	11/30/99	Klee et al.			
SBG	ES	6,146,906	11/14/00	Inoue et al.			
SBG	ET	6,180,252 B1	01/30/01	Farrell et al.			
SBG	EV	4,876,219	10/24/89	Eshita et al.			
SBG	EW	5,391,515	02/21/95	Kao et al.			
SBG	EX	4,963,508	10/16/90	Umeno et al.			
SBG	EY	5,063,166	11/05/91	Mooney et al.			
SBG	EZ	5,356,831	10/18/94	Calviello et al.			
SBG	FA	5,777,762	07/07/98	Yamamoto			
SBG	FB	5,778,116	07/07/98	Tomich			
SBG	FC	5,127,067	06/30/92	Delcoco et al.			
SBG	FD	5,861,966	01/19/99	Ortel			
SBG	FE	6,137,603	10/24/00	Henmi			
SBG	FF	5,858,814	01/12/99	Goossen et al.			
SBG	FG	5,778,018	07/07/98	Yoshikawa et al.			
SBG	FH	5,764,676	06/09/98	Paoli et al.			
SBG	FI	5,729,394	03/17/98	Sevier et al.			
SBG	FJ	5,883,996	03/16/99	Knapp et al.			
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FOREIGN PATENT DOCUMENTS							
		NUMBER	DATE	COUNTRY	TRANSLATION		
					YES	NO	
SBC	AAA	0 250 171	12/23/87	EP	X		
SBC	AAB	0 342 937	11/23/89	EP	X		
SBC	AAC	0 455 526	06/11/91	EP	X		
SBC	AAD	0 602 568	06/22/94	EP	X		
SBC	AAE	0 607 435	07/27/94	EP	X		
SBC	AAF	1 001 468	05/17/00	EP	X		
SBC	AAG	0 514 018	11/19/92	EP	X		
SBC	AAH	0 999 600	05/10/00	EP	X		
SBC	AAI	1 319 311	06/04/70	Great Britain	X		
SBC	AAJ	10-321943	12/04/98	Japan			
SBC	AAK	11-238683	08/31/99	Japan	X		
SBC	AAL	11-260835	09/24/99	Japan w/English Abstract	X		
SBC	AAM	HEI 2-391	01/05/90	Japan w/English Abstract	X		
SBC	AAN	5-48072	02/26/93	Japan w/English Abstract	X		
SBC	AAO	52-88354	07/23/77	Japan	X		
SBC	AAP	54-134554	10/19/79	Japan	X		
SBC	AAQ	55-87424	07/02/80	Japan	X		
SBC	AAR	61-108187	05/26/86	Japan w/English Abstract	X		
SBC	AAS	6-232126	08/19/94	Japan	X		
SBC	AAT	6-291299	10/18/94	Japan w/English Abstract	X		
SBC	AAU	63-34994	02/15/88	Japan w/English Abstract	X		
SBC	AAV	63-131104	06/03/88	Japan w/English Abstract	X		
SBC	AAW	63-198365	08/18/88	Japan	X		
SBC	AAX	63-278629	01/05/90	Japan	X		
SBC	AAZ	6-33 4168	12/02/94	Japan	X		
SBC	AAZ	WO 99/63580	12/09/99	WIPO	X		
SBC	BAA	WO 99/14804	03/25/99	WIPO	X		
SBC	BBB	WO 97/45827	12/04/97	WIPO			
SBC	BBC	WO 99/19546	04/22/99	WIPO			
SBC	BBD	WO 00/33363	06/08/00	WIPO			
SBC	BBE	WO 00/48239	08/17/00	WIPO			
SBC	BBF	WO 99/14797	03/25/99	WIPO			
SBC	BBG	GB 2 335 792	09/29/99	Great Britain			
	BBH						
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
SBG	CAA	Nakagawara et al., "Effects of Buffer Layers in Epitaxial Growth of SrTiO <sub>3</sub> Thin Film on Si(100), <i>J. Appl. Phys.</i> , 78 (12), December 15, 1995, pp. 7226-7230.					
SBG	CBB	Suzuki et al., "A Proposal of Epitaxial Oxide Thin Film Structures For Future Oxide Electronics," <i>Materials Science and Engineering B41</i> , (1996), pp. 166-173.					
SBG	CCC	W. F. Egelhoff et al., "Optimizing GMR Spin Valves: The Outlook for Improved Properties", <i>1998 Int'l Non Volatile Memory Technology Conference</i> , pp. 34-37.					
SBG	CCD	Wang et al., "Processing and Performance of Piezoelectric Films", Univ. Of MD, Wilcoxon Research Col, and Motorola Labs, May 11, 2000.					
SBG	CCE	M. Rotter et al., "Nonlinear Acoustoelectric Interactions in GaAs/LiNbO <sub>3</sub> Structures", <i>Applied Physics Letters</i> , Vol. 75(7), August 16, 1999, pp. 965-967.					
SBG	CCF	K. Sreenivas et al., "Surface Acoustic Wave Propagation on Lead Zirconate Titanate Thin Films," <i>Appl. Phys. Lett.</i> 52 (9), Feb. 29, 1998, pp. 709-711.					
SBG	CCG	M. Rotter et al., "Single Chip Fused Hybrids for Acousto-Electric and Acousto-Optic Applications," <i>1997 Applied Physics Letters</i> , Vol. 70(16), April 21, 1997, pp. 2097-2099.					
SBG	CCH	A. Mansingh et al., "Surface Acoustic Wave Propagation in PZT/YBCO/SrTiO <sub>3</sub> and PbTiO <sub>3</sub> /YBCO/SrTiO <sub>3</sub> Epitaxial Heterostructures," <i>Ferroelectric</i> , Vol. 224, pages 275-282, 1999.					
SBG	CCI	S. Mathews et al., "Ferroelectric Field Effect Transistor Based on Epitaxial Perovskite Heterostructures", <i>Science</i> , Vol. 276, April 11, 1997, pp. 238-240.					
SBG	CCJ	R. Houdre et al., "Properties of GaAs on Si Grown by Molecular Beam Epitaxy," <i>Solid State and Materials Sciences</i> , Vol. 16, Issue 2, 1990, pp. 91-114.					
SBG	CCK	S. F. Fang et al., "Gallium Arsenide and Other Compound Semiconductors on Silicon," <i>J. Appl. Phys.</i> , 68(7), October 1, 1990, pp. R31-R58.					
SBG	CCL	Carlin et al., "Impact of GaAs Buffer Thickness on Electronic Quality of GaAs Grown on Graded Ge/GeSi/Si Substrates," <i>Appl. Phys. Letter</i> , Vol. 76, No. 14, April 2000, pp. 1884-1886.					
SBG	CCM	Ringel et al., "Epitaxial Integration of III-V Materials and Devices with Si Using Graded GeSi Buffers," <i>27<sup>th</sup> International Symposium on Compound Semiconductors</i> , Oct. 2000.					
SBG	CCN	Zogg et al., "Progress in Compound-Semiconductor-on-Silicon-Heteroepitaxy with Fluoride Buffer Layers," <i>J. Electrochem Soc.</i> , Vol. 136, No. 3, March 1998, pp. 775-779.					
SBG	CCO	Xiong et al., "Oxide Defined GaAs Vertical-Cavity Surface-Emitting Lasers on Si Substrates," <i>IEEE Photonics Technology Letters</i> , Vol. 12, No. 2, Feb. 2000, pp. 110-112.					
SBG	CCP	Clem et al., "Investigation of PZT//LSCO//Pt//Aerogel Thin Film Composites for Uncooled Pyroelectric IR Detectors," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 541, pp. 661-666, 1999.					
SBG	CCQ	Gunapala et al., "Bound-To-Quasi-Bound Quantum-Well Infrared Photodetectors," <i>NASA Tech Brief</i> , Vol. 22, No. 9, September 1998.					
Examiner				Date Considered		4/16/02	
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
SBC	DAA	Brown et al., "Photodetectors: Materials and Devices II," <i>Intn. Society for Optical Engineering</i> , Vol. 2999, pp. 211-224.					
SBC	DAB	Bruley et al., "Nanostructure and Chemistry of a (100)MgO/(100) GaAs Interface," <i>Appl. Phys Lett</i> , 65(5), Aug. 1994, pp. 564-566.					
SBC	DAC	Fork et al., "Epitaxial MgO On Si(001) for Y-Ba-Cu-O Thin Film Growth by Pulsed Laser Deposition," <i>Appl. Phys Lett.</i> , 58(20), May 20, 1991, pp. 2294-2296.					
SBC	DAD	Himpfel et al., "Dialectrics on Semiconductors," <i>Materials Science and Engineering</i> , B1(1988), pp. 9-13.					
SBC	DAE	Li et al., "Epitaxial $\text{La}_{0.67}\text{Sr}_{0.33}\text{MnO}_3$ Magnetic Tunnel Junctions," <i>J. Appl. Phys.</i> 81(8), Apr. 15, 1997, pp. 5509-5511.					
SBC	DAF	O'Donnell et al., "Colossal Magnetoresistance Magnetic Tunnel Junctions Grown by Molecular-Beam Epitaxy," <i>Appl. Physics Letters</i> , Vol. 76, No. 14, April 3, 2000, pp. 1914-1916.					
SBC	DAG	Mikami et al., "Formation of Si Epi/MgO-Al <sub>2</sub> O <sub>3</sub> Epi./SiO <sub>2</sub> /Si and Its Epitaxial Film Quality," <i>Fundamental Research Laboratories and Microelectronics Laboratories</i> , pp. 31-34, 1983.					
SBC	DAH	T. Asano et al., "An Epitaxial Si/Insulator/Si Structure Prepared by Vacuum Deposition of CaF <sub>2</sub> and Silicon," <i>Thin Solid Films</i> , Vol. 93 (1982), pp. 143-150.					
SBC	DAI	T. Chikyow et al., "Reaction and Regrowth Control of CeO <sub>2</sub> on Si(111) Surface for the Silicon-On-Insulator Structure," <i>Appl. Phys. Lett.</i> , Vol. 65, No. 8, 22 August 1994, pp. 1030-1032.					
SBC	DAJ	J.F. Kang, et al., "Epitaxial Growth of CeO <sub>2</sub> (100) Films on Si(100) Substrates by Dual Ion Beams Reactive Sputtering," <i>Solid State Communications</i> , Vol. 108, No. 4, pp. 225-227, 1998.					
SBC	DAK	R.A. Morgan et al., "Vertical-Cavity Surface-Emitting Lasers Come of Age," <i>SPIE</i> , Vol. 2683, pp. 18-29.					
SBC	DAL	"Technical Analysis of Qualcomm QCP-800 Portable Cellular Phone (Transmitter Circuitry)," Talus Corporation, Qualcomm QCP-800 Technical Analysis Report, December 10, 1996, pp. 5-8.					
SBC	DAM	Jo-Ey WONG, et al.; "AN ELECTROSTATICALLY-ACTUATED MEMS SWITCH FOR POWER APPLICATIONS"; IEEE, 2000; pp. 633-638					
SBC	DAN	T. MIZUNO, et al.; "Electron and Hole Mobility Enhancement in Strained-Si MOSFET's on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology"; IEEE ELECTRON DEVICE LETTERS, VOL. 21, NO. 5, MAY 2000; pp. 230-232					
SBC	DAO	F.M. BUFFER, et al.; "Strain-dependence of electron transport in bulk Si and deep-submicron MOSFET's" <i>Computational Electronics</i> , 2000, Book of Abstracts, IWCE Glasgow 2000, 7 <sup>th</sup> Int'l Workshop on, 2000, pp. 64-65					
SBC	DAP	S.S. LU, et al.; "Piezoelectric field effect transistor (PEFET) using $\text{In}_{0.2}\text{Ga}_{0.8}\text{As}/\text{Al}_{0.35}\text{Ga}_{0.65}\text{As}/\text{In}_{0.2}\text{Ga}_{0.8}\text{As}/\text{GaAs}$ Strained layer structure on (111)B GaAs substrate"; <i>ELECTRONICS LETTERS</i> , 12 <sup>th</sup> Ma 1994, Vol. 30, No. 10; pp. 823-825					
SBC	DAQ	Kihong KIM, et al." On-Chip Wireless Interconnection with Integrated Antennas"; 2000 IEEE; pp. 20.2.1-20.3.4					
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SBG-	EAA	G. PASSINO <del>PADESI</del> et al.; "V-BAND SINGLE CHIP, DIRECT CARRIER BPSK MODULATION TRANSMITTER WITH INTEGRATED PATCH ANTENNA"; 1998 IEEE MTT-S DIGEST; pp. 305-308					
SBG-	EAB	Mau-Chung Frank CHANG, et al.; "RF/Wireless Interconnect for Inter- and Intra-Chip Communications"; Proceedings of the IEEE, Vol. 89, No. 4, April 2001; pp. 456-466					
SBG-	EAC	The Electronics Industry Report, Prismark; 2001; pp. 111-120					
SBG-	EAD	J.K. ABROKWAH, et al.; "A Manufacturable Complementary GaAs Process"; GaAs IC Symposium, IEEE, 1993; pp. 127-130					
SBG-	EAE	H. Nagata, "A Preliminary Consideration of the Growth Behaviour of CeO <sub>2</sub> , SrTiO <sub>3</sub> and SrVO <sub>3</sub> Films on Si Substrate," <i>Thin Solid Films</i> , 224, 1993, pp. 1-3.					
SBG-	EAF	Nagata et al., "Heteroepitaxial Growth of CeO <sub>2</sub> (001) Films on Si(001) Substrates by Pulsed Laser Deposition in Ultrahigh Vacuum," <i>Jpn. Jour. Appl. Phys.</i> , Vol. 30, No. 6B, June 1991, pp. L1136-L1138.					
SBG-	EAG	Kado et al., "Heteroepitaxial Growth of SrO Films on Si Substrates," <i>J. Appl. Phys.</i> , 61(6), March 15, 1987, pp. 2398-2400.					
SBG-	EAH	Bean et al., "Silicon Molecular Beam Epitaxy," <i>Materials Research Symposium Proceedings</i> , Vol. 220, pp. 595-600, April 29 - May 3, 1991.					
SBG-	EAI	J.K. Abrokwhah, et al.; "A Manufacturable High-Speed Low-Power Complementary GaAs Process"; Extended Abstracts of the 1994 International Conference on Solid State Devices and Materials, Yokohama, 1994, pp.592-594					
SBG-	EAJ	Leonard J. BRILLSON; "Stable and Epitaxial Contacts to III-V Compound Semiconductors"; Semiconductors Fundamentals and Technology; Noyles Publications, 1993; pp.67-150					
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